

### **isc Silicon NPN Power Transistor**

## 2SD641

### DESCRIPTION

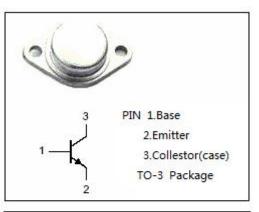
- Collector-Emitter Breakdown Voltage-
  - :  $V_{(BR)CEO}$ = 400V (Min)
- Low Collector-Emitter Saturation Voltage-
  - : V<sub>CE(sat)</sub>= 1.5V (Max.)@ I<sub>C</sub>= 10A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

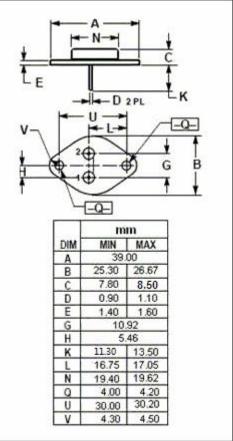
### **APPLICATIONS**

- High voltage switching applications.
- High power amplifier applications.

| SYMBOL           | PARAMETER                               | МАХ     | UNIT |
|------------------|---|---------|------|
| V <sub>CBO</sub> | Collector-Base Voltage                  | 600     | V    |
| Vceo             | Collector-Emitter Voltage               | 400     | V    |
| V <sub>EBO</sub> | Emitter-Base Voltage                    | ge 5    |      |
| lc               | Collector Current-Continuous            | 15      | А    |
| l <sub>Β</sub>   | Base Current-Continuous                 | 5       | А    |
| Pc               | Collector Power Dissipation<br>@Tc=25°C | 150     | W    |
| Tj               | Junction Temperature                    | 150     | °C   |
| T <sub>stg</sub> | Storage Temperature Range               | -65~150 | °C   |

# ABSOLUTE MAXIMUM RATINGS(Ta=25°C)





isc website: www.iscsemi.com



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### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}\text{=}25\,^{\circ}\!\!\!\!\!\!\mathrm{C}$  unless otherwise specified

| SYMBOL               | PARAMETER                            | CONDITIONS                                 | MIN | TYP. | МАХ | UNIT |
|----------------------|--------------------------------------|--|-----|------|-----|------|
| V <sub>(BR)CEO</sub> | Collector-Emitter Breakdown Voltage  | I <sub>C</sub> = 20mA; I <sub>B</sub> = 0  | 400 |      |     | V    |
| V <sub>CE(sat)</sub> | Collector-Emitter Saturation Voltage | I <sub>C</sub> = 10A; I <sub>B</sub> = 2A  |     |      | 1.5 | V    |
| V <sub>BE(sat)</sub> | Base-Emitter Saturation Voltage      | I <sub>C</sub> = 10A; I <sub>B</sub> = 2A  |     |      | 2.0 | V    |
| I <sub>CBO</sub>     | Collector Cutoff Current             | V <sub>CB</sub> = 500V; I <sub>E</sub> = 0 |     |      | 0.5 | mA   |
| І <sub>ЕВО</sub>     | Emitter Cutoff Current               | V <sub>EB</sub> = 5V; I <sub>C</sub> = 0   |     |      | 1.0 | mA   |
| h <sub>FE</sub>      | DC Current Gain                      | I <sub>C</sub> = 5A; V <sub>CE</sub> = 5V  | 20  |      | 140 |      |

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